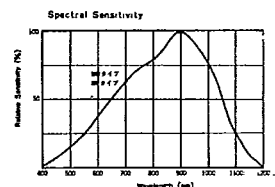


# SILICON PLANAR PHOTODIODES

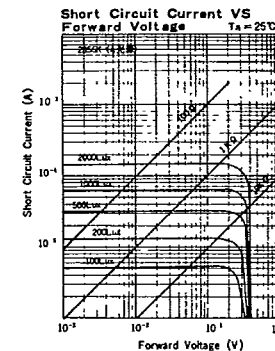
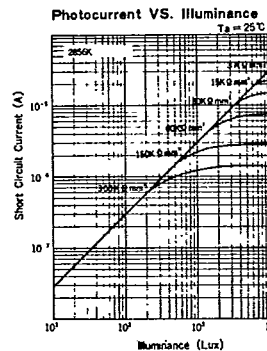
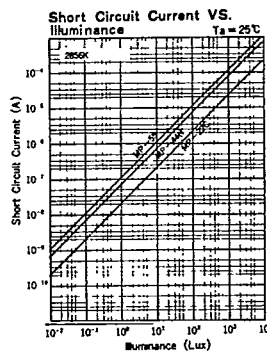
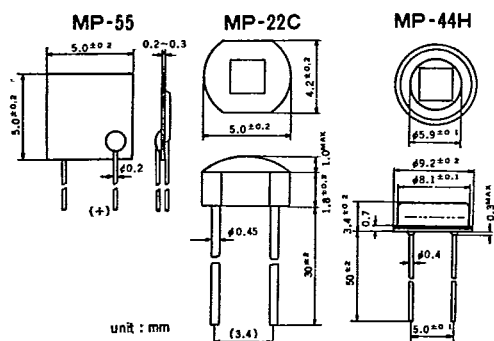
## Maximum Ratings

Ratings	Symbol	MP-55	MP-22C	MP-44H	Units
Reverse Voltage	$V_R$	30	30	30	V
Power Dissipation	P	0.3	0.05	0.2	mW
Operating Temperature	Topr.		- 0 ~ + 70		°C
Storage Temperature	Tstg		- 20 ~ + 80		°C



## Characteristics

Ratings	Symbol	Conditions	MP-55		MP-22C		MP-44H		Units
			MIN.	TYP. MAX.	MIN.	TYP. MAX.	MIN.	TYP. MAX.	
Short Circuit Current	$I_{sc}$	2856K 1000Lux	70	110	20	28	45	70	$\mu A$
Dark Current	$I_d$	$V_R = 1 V R_H < 65\%$	1	50	0.5	15	1	30	nA
Open Circuit Voltage	$V_{oc}$	2856 K 1000Lux	450		450		450		mV
Peak Sensitivity Wavelength	$\lambda_p$		900		900		900		nm
Response Time	tr, tf	1000Lux $R_S = 1 k\Omega$	8		2		5		$\mu s$
Temp. Coefficient of $I_{sc}$		2856 K 1000Lux	0.17		0.17		0.17		%/°C
Temp. Coefficient of $V_{oc}$		2856 K 1000Lux	- 3.0		- 3.3		- 3.0		mV/°C

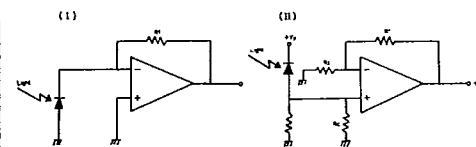


# SILICON BLUE-SENSITIVE PHOTODIODES

## Maximum Ratings

Ratings	Symbol	MBC-2014CF	MBC-3026CF	Units
Reverse Voltage	$V_R$	10	10	V
Operating Temperature	Topr.	- 20 ~ + 60		°C
Storage Temperature	Tstg	- 20 ~ + 80		°C

Ta = 25°C



## Characteristics

Ratings	Symbol	Conditions	MBC-2014CF		MBC-3026CF		Units
			MIN.	TYP. MAX.	MIN.	TYP. MAX.	
Short Circuit Current	$I_{sc}$	2856K 100Lux	120	170	400	550	nA
Dark Current	$I_d$	$V_R = 1 V R_H < 65\%$	1	10	3	10	pA
Open Circuit Voltage	$V_{oc}$	2856K 100Lux	140		140		mV
Peak Sensitivity Wavelength	$\lambda_p$		560	600	560	600	nm
Terminal Capacitance	$C_t$	$V_R = 1 V f = 1 MHz$	250	500	600	1400	pF
Temp. Coefficient of $I_{sc}$		2856K 100Lux	0.07		0.07		%/°C
Temp. Coefficient of $I_d$		$V_R = 1 V R_H \leq 65\%$	5		5		/10°C

